

AMENDMENTS TO THE ABSTRACT:

Please amend the Abstract as follows:

~~The invention discloses that a~~A nitride semiconductor laser element exhibits is able to comply with requirement of high-speed responsiveness by largely reducing the capacitance of the nitride semiconductor laser element. The nitride semiconductor laser element includes an n-type semiconductor layer, an active layer (205) and a p-type semiconductor layer each laminated on the main surface of the substrate. ~~substrate (101) and comprising a~~The nitride semiconductor laser element further includes nitride, wherein a striped ridge portion (2) is formed in the p-type semiconductor layer, and pn-junctions of the semiconductor layer in the peripheral region remote from the ridge portion are broken by ion implantation to form an insulative region (1) for reducing the capacitance of the element.